

Hongxing Jiang

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

386
papers

15,463
citations

65
h-index

107
g-index

426
ext. papers

16,745
ext. citations

3.2
avg, IF

6.4
L-index

#	Paper	IF	Citations
386	Deep ultraviolet photoluminescence of water-soluble self-passivated graphene quantum dots. <i>ACS Nano</i> , 2012 , 6, 5102-10	16.7	1323
385	Deep ultraviolet to near-infrared emission and photoresponse in layered N-doped graphene quantum dots. <i>ACS Nano</i> , 2014 , 8, 6312-20	16.7	384
384	Band structure and fundamental optical transitions in wurtzite AlN. <i>Applied Physics Letters</i> , 2003 , 83, 5163-5165	3.4	282
383	III-nitride blue and ultraviolet photonic crystal light emitting diodes. <i>Applied Physics Letters</i> , 2004 , 84, 466-468	3.4	279
382	InGaN/GaN multiple quantum well solar cells with long operating wavelengths. <i>Applied Physics Letters</i> , 2009 , 94, 063505	3.4	274
381	Unique optical properties of AlGaN alloys and related ultraviolet emitters. <i>Applied Physics Letters</i> , 2004 , 84, 5264-5266	3.4	269
380	Structural phase behavior in II-VI semiconductor nanoparticles. <i>Applied Physics Letters</i> , 1995 , 67, 831-833	3.4	216
379	III-nitride blue microdisplays. <i>Applied Physics Letters</i> , 2001 , 78, 1303-1305	3.4	209
378	Mg acceptor level in AlN probed by deep ultraviolet photoluminescence. <i>Applied Physics Letters</i> , 2003 , 83, 878-880	3.4	204
377	III-Nitride full-scale high-resolution microdisplays. <i>Applied Physics Letters</i> , 2011 , 99, 031116	3.4	198
376	Fundamental optical transitions in GaN. <i>Applied Physics Letters</i> , 1996 , 68, 2784-2786	3.4	165
375	Epitaxially grown semiconducting hexagonal boron nitride as a deep ultraviolet photonic material. <i>Applied Physics Letters</i> , 2011 , 98, 211110	3.4	156
374	InGaN/GaN multiple quantum well concentrator solar cells. <i>Applied Physics Letters</i> , 2010 , 97, 073115	3.4	147
373	200nm deep ultraviolet photodetectors based on AlN. <i>Applied Physics Letters</i> , 2006 , 89, 213510	3.4	146
372	Time-resolved photoluminescence studies of In _x Ga _{1-x} As _{1-y} N _y . <i>Applied Physics Letters</i> , 2000 , 76, 188-190	3.4	146
371	Deep impurity transitions involving cation vacancies and complexes in AlGaN alloys. <i>Applied Physics Letters</i> , 2005 , 86, 222108	3.4	143
370	Nitride deep-ultraviolet light-emitting diodes with microlens array. <i>Applied Physics Letters</i> , 2005 , 86, 173504	3.4	142

369	GaN microdisk light emitting diodes. <i>Applied Physics Letters</i> , 2000 , 76, 631-633	3.4	140
368	Optical and electrical properties of Mg-doped p-type Al _x Ga _{1-x} N. <i>Applied Physics Letters</i> , 2002 , 80, 1210-1212	3.4	138
367	Nitride micro-LEDs and beyond--a decade progress review. <i>Optics Express</i> , 2013 , 21 Suppl 3, A475-84	3.3	137
366	Metastability and persistent photoconductivity in Mg-doped p-type GaN. <i>Applied Physics Letters</i> , 1996 , 68, 1808-1810	3.4	137
365	Nature of Mg impurities in GaN. <i>Applied Physics Letters</i> , 1996 , 69, 1474-1476	3.4	130
364	Dependence of Ni/AlGa _N Schottky barrier height on Al mole fraction. <i>Journal of Applied Physics</i> , 2000 , 87, 801-804	2.5	126
363	Structure and Photoluminescence Study of TiO ₂ Nanoneedle Texture along Vertically Aligned Carbon Nanofiber Arrays. <i>Journal of Physical Chemistry C</i> , 2008 , 112, 17127-17132	3.8	122
362	Temperature and compositional dependence of the energy band gap of AlGa _N alloys. <i>Applied Physics Letters</i> , 2005 , 87, 242104	3.4	122
361	Photoluminescence studies of impurity transitions in Mg-doped AlGa _N alloys. <i>Applied Physics Letters</i> , 2009 , 94, 091903	3.4	120
360	Enhanced light extraction in III-nitride ultraviolet photonic crystal light-emitting diodes. <i>Applied Physics Letters</i> , 2004 , 85, 142-144	3.4	117
359	Mechanisms of band-edge emission in Mg-doped p-type GaN. <i>Applied Physics Letters</i> , 1996 , 68, 1883-1885	3.4	117
358	Hydrogen generation by solar water splitting using p-InGa _N photoelectrochemical cells. <i>Applied Physics Letters</i> , 2010 , 96, 052110	3.4	116
357	III-nitride photonic crystals. <i>Applied Physics Letters</i> , 2003 , 83, 1231-1233	3.4	115
356	Time-resolved photoluminescence studies of Al _x Ga _{1-x} N alloys. <i>Applied Physics Letters</i> , 2000 , 76, 1252-1254	3.4	110
355	Photoluminescence studies of impurity transitions in AlGa _N alloys. <i>Applied Physics Letters</i> , 2006 , 89, 092107	3.4	103
354	Correlation between optoelectronic and structural properties and epilayer thickness of AlN. <i>Applied Physics Letters</i> , 2007 , 90, 241101	3.4	100
353	InGa _N /Ga _N quantum well interconnected microdisk light emitting diodes. <i>Applied Physics Letters</i> , 2000 , 77, 3236-3238	3.4	100
352	Transport properties of highly conductive n-type Al-rich Al _x Ga _{1-x} N (x>0.7). <i>Applied Physics Letters</i> , 2004 , 85, 3769-3771	3.4	99

- 351 Enhanced p-type conduction in GaN and AlGa_N by Mg-doping. *Applied Physics Letters*, **2003**, 82, 3041-3043 99
- 350 Electrical and optical properties of Mg-doped Al_{0.7}Ga_{0.3}N alloys. *Applied Physics Letters*, **2005**, 86, 092108 99
- 349 Dielectric strength, optical absorption, and deep ultraviolet detectors of hexagonal boron nitride epilayers. *Applied Physics Letters*, **2012**, 101, 171112 3-4 95
- 348 Correlation between optical and electrical properties of Mg-doped AlN epilayers. *Applied Physics Letters*, **2006**, 89, 152120 3-4 95
- 347 Time-resolved photoluminescence studies of InGa_N epilayers. *Applied Physics Letters*, **1996**, 69, 2837-2839 95
- 346 Hexagonal boron nitride for deep ultraviolet photonic devices. *Semiconductor Science and Technology*, **2014**, 29, 084003 1.8 93
- 345 Hexagonal boron nitride epitaxial layers as neutron detector materials. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2011**, 654, 417-420 1.2 93
- 344 Piezoelectric effects on the optical properties of GaN/Al_xGa_{1-x}N multiple quantum wells. *Applied Physics Letters*, **1998**, 73, 3426-3428 3-4 93
- 343 Quantum-confined Stark effects in semiconductor quantum dots. *Physical Review B*, **1995**, 52, 5913-5923 3 93
- 342 Thermoelectric properties of In_xGa_{1-x}N alloys. *Applied Physics Letters*, **2008**, 92, 042112 3-4 91
- 341 Persistent photoconductivity in a two-dimensional electron gas system formed by an AlGa_N/Ga_N heterostructure. *Journal of Applied Physics*, **1997**, 82, 1227-1230 2.5 89
- 340 Optical and electrical properties of Al-rich AlGa_N alloys. *Applied Physics Letters*, **2001**, 79, 3245-3247 3-4 88
- 339 Polarization of III-nitride blue and ultraviolet light-emitting diodes. *Applied Physics Letters*, **2005**, 86, 091107 87
- 338 Band-edge photoluminescence of AlN epilayers. *Applied Physics Letters*, **2002**, 81, 3365-3367 3-4 87
- 337 Deep ultraviolet picosecond time-resolved photoluminescence studies of AlN epilayers. *Applied Physics Letters*, **2003**, 82, 1694-1696 3-4 86
- 336 Effects of tensile and compressive strain on the luminescence properties of Al_{0.5}In_{0.5}Ga_N/InGa_N quantum well structures. *Applied Physics Letters*, **2000**, 77, 821-823 3-4 85
- 335 Nature of deep center emissions in GaN. *Applied Physics Letters*, **2010**, 96, 151902 3-4 84
- 334 Relaxation of persistent photoconductivity in Al_{0.3}Ga_{0.7}As. *Physical Review B*, **1990**, 42, 5855-5858 3-3 83

333	III-nitride micro-emitter arrays: development and applications. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 094001	3	80
332	Percolation transition of persistent photoconductivity in II-VI mixed crystals. <i>Physical Review Letters</i> , 1990 , 64, 2547-2550	7.4	80
331	Quantum shift of band-edge stimulated emission in InGaN/GaN multiple quantum well light-emitting diodes. <i>Applied Physics Letters</i> , 1997 , 70, 2978-2980	3.4	79
330	Direct hydrogen gas generation by using InGaN epilayers as working electrodes. <i>Applied Physics Letters</i> , 2008 , 93, 162107	3.4	78
329	Epitaxial growth and demonstration of hexagonal BN/AlGaN p-n junctions for deep ultraviolet photonics. <i>Applied Physics Letters</i> , 2012 , 100, 061121	3.4	76
328	A study of the Au/Ni ohmic contact on p-GaN. <i>Journal of Applied Physics</i> , 2000 , 88, 4196	2.5	76
327	AlGaN-based ultraviolet light-emitting diodes grown on AlN epilayers. <i>Applied Physics Letters</i> , 2004 , 85, 4777-4779	3.4	74
326	Development of microLED. <i>Applied Physics Letters</i> , 2020 , 116, 100502	3.4	73
325	Band-edge exciton states in AlN single crystals and epitaxial layers. <i>Applied Physics Letters</i> , 2004 , 85, 4334	3.4	68
324	Growth and optical properties of In _x Al _y Ga _{1-x-y} N quaternary alloys. <i>Applied Physics Letters</i> , 2001 , 78, 61-63	3.4	68
323	Growth of III-nitride photonic structures on large area silicon substrates. <i>Applied Physics Letters</i> , 2006 , 88, 171909	3.4	67
322	Excitonic recombination in GaN grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1995 , 67, 3387-3389	3.4	67
321	Al _x Ga _{1-x} N/GaN band offsets determined by deep-level emission. <i>Journal of Applied Physics</i> , 2001 , 90, 1887-1890	2.5	64
320	Two-dimensional excitons in three-dimensional hexagonal boron nitride. <i>Applied Physics Letters</i> , 2013 , 103, 191106	3.4	63
319	Achieving highly conductive AlGaN alloys with high Al contents. <i>Applied Physics Letters</i> , 2002 , 81, 1038-1040	3.4	63
318	The origin of deep-level impurity transitions in hexagonal boron nitride. <i>Applied Physics Letters</i> , 2015 , 106, 021110	3.4	61
317	Electroluminescent properties of erbium-doped III-N light-emitting diodes. <i>Applied Physics Letters</i> , 2004 , 84, 1061-1063	3.4	61
316	Effects of well thickness and Si doping on the optical properties of GaN/AlGaN multiple quantum wells. <i>Applied Physics Letters</i> , 1997 , 71, 1368-1370	3.4	58

315	Optical transitions in GaN/Al _x Ga _{1-x} N multiple quantum wells grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1996 , 69, 2453-2455	3-4	58
314	Fabrication of n-type nickel doped B5C1+homojunction and heterojunction diodes. <i>Applied Physics Letters</i> , 1997 , 70, 1028-1030	3-4	57
313	Exciton localization in AlGa _n alloys. <i>Applied Physics Letters</i> , 2006 , 88, 062103	3-4	57
312	Optical modes within III-nitride multiple quantum well microdisk cavities. <i>Applied Physics Letters</i> , 1998 , 72, 1530-1532	3-4	57
311	Electrical and optical properties of p-type InGa _n . <i>Applied Physics Letters</i> , 2009 , 95, 261904	3-4	56
310	Realization of highly efficient hexagonal boron nitride neutron detectors. <i>Applied Physics Letters</i> , 2016 , 109, 072101	3-4	55
309	III-nitride ultraviolet light-emitting diodes with delta doping. <i>Applied Physics Letters</i> , 2003 , 83, 566-568	3-4	54
308	Properties of Co-, Cr-, or Mn-implanted AlN. <i>Journal of Applied Physics</i> , 2003 , 94, 1592-1596	2-5	54
307	Optical resonance modes in GaN pyramid microcavities. <i>Applied Physics Letters</i> , 1999 , 75, 763-765	3-4	54
306	Room temperature intrinsic optical transition in GaN epilayers: The band-to-band versus excitonic transitions. <i>Applied Physics Letters</i> , 1997 , 71, 635-637	3-4	53
305	Exciton-phonon interaction in InGa _n /Ga _n and Ga _n /AlGa _n multiple quantum wells. <i>Applied Physics Letters</i> , 1997 , 70, 2882-2884	3-4	53
304	Erbium-doped GaN epilayers synthesized by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2006 , 89, 151903	3-4	53
303	Optical properties of AlN and Ga _n in elevated temperatures. <i>Applied Physics Letters</i> , 2004 , 85, 3489-3491	3-4	53
302	GaN-based waveguide devices for long-wavelength optical communications. <i>Applied Physics Letters</i> , 2003 , 82, 1326-1328	3-4	51
301	Neutral-donor-bound exciton recombination dynamics in Ga _n grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1995 , 67, 1653-1655	3-4	51
300	Persistent photoconductivity in Ga _{1-x} In _x NyAs _{1-y} . <i>Applied Physics Letters</i> , 1999 , 75, 1899-1901	3-4	50
299	Photoluminescence studies of band-edge transitions in Ga _n epitaxial layers grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1996 , 79, 2675-2683	2-5	50
298	Persistent photoconductivity and related critical phenomena in Zn _{0.3} Cd _{0.7} Se. <i>Physical Review B</i> , 1989 , 40, 10025-10028	3-3	49

297	Comparison of optical transitions in InGaN quantum well structures and microdisks. <i>Journal of Applied Physics</i> , 2001 , 89, 4951-4954	2.5	48
296	Kinetics of persistent photoconductivity in Al _{0.3} Ga _{0.7} As and Zn _{0.3} Cd _{0.7} Se semiconductor alloys. <i>Physical Review B</i> , 1992 , 45, 13996-14004	3.3	48
295	Single phase In _x Ga _{1-x} N (0.25 ≤ x ≤ 0.63) alloys synthesized by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2008 , 93, 182107	3.4	47
294	Band structure of superlattice with graded interfaces. <i>Journal of Applied Physics</i> , 1987 , 61, 624-628	2.5	47
293	Review Hexagonal Boron Nitride Epilayers: Growth, Optical Properties and Device Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q3012-Q3021	2	46
292	Mechanism of enhanced luminescence in In _x Al _y Ga _{1-x-y} N quaternary alloys. <i>Applied Physics Letters</i> , 2002 , 80, 1397-1399	3.4	45
291	Free excitonic transitions in GaN, grown by metal-organic chemical-vapor deposition. <i>Journal of Applied Physics</i> , 1996 , 79, 7001-7004	2.5	45
290	Linewidths of excitonic luminescence transitions in AlGaIn alloys. <i>Applied Physics Letters</i> , 2001 , 78, 1829-1831	3.4	44
289	Hexagonal boron nitride thin film thermal neutron detectors with high energy resolution of the reaction products. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2015 , 783, 121-127	1.2	43
288	Fabrication and characterization of solid-state thermal neutron detectors based on hexagonal boron nitride epilayers. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2014 , 748, 84-90	1.2	43
287	Optical and electrical properties of Mg-doped AlN nanowires grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2015 , 106, 213105	3.4	43
286	Ultraviolet photoluminescence from Gd-implanted AlN epilayers. <i>Applied Physics Letters</i> , 2006 , 89, 1521074	3.4	43
285	Suppression of thermal conductivity in In _x Ga _{1-x} N alloys by nanometer-scale disorder. <i>Applied Physics Letters</i> , 2013 , 102, 121906	3.4	42
284	1.54 μ m emitters based on erbium doped InGaIn p-i-n junctions. <i>Applied Physics Letters</i> , 2010 , 97, 141109	3.4	42
283	Erbium-doped GaN optical amplifiers operating at 1.54 μ m. <i>Applied Physics Letters</i> , 2009 , 95, 111109	3.4	42
282	Band-edge transitions in hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2012 , 101, 051110	3.4	42
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280	Nitride microlens arrays for blue and ultraviolet wavelength applications. <i>Applied Physics Letters</i> , 2003 , 82, 3692-3694	3.4	42

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277	The origins of leaky characteristics of Schottky diodes on p-GaN. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 292-296	2-9	41
276	The incorporation of Nickel and Phosphorus dopants into Boron-Carbon alloy thin films. <i>Applied Physics A: Materials Science and Processing</i> , 1998 , 67, 335-342	2-6	40
275	Excitonic luminescence linewidths in AlGa _x N alloys with high aluminum concentrations. <i>Applied Physics Letters</i> , 2002 , 80, 2907-2909	3-4	40
274	Optical properties of GaN pyramids. <i>Applied Physics Letters</i> , 1999 , 74, 1227-1229	3-4	40
273	Optical resonance modes in InGa _x N/GaN multiple-quantum-well microring cavities. <i>Applied Physics Letters</i> , 1999 , 75, 2563-2565	3-4	40
272	Dynamics of a band-edge transition in GaN grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1995 , 66, 3474-3476	3-4	40
271	Optical polarization in c-plane Al-rich Al _x Ga _{1-x} N single quantum wells. <i>Applied Physics Letters</i> , 2012 , 101, 042103	3-4	39
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268	Size dependence of III-nitride microdisk light-emitting diode characteristics. <i>Applied Physics Letters</i> , 2001 , 78, 3532-3534	3-4	38
267	Photoresponsivity of ultraviolet detectors based on In _x Al _y Ga _{1-x-y} N quaternary alloys. <i>Applied Physics Letters</i> , 2000 , 77, 791-793	3-4	38
266	Well-width dependence of the quantum efficiencies of GaN/Al _x Ga _{1-x} N multiple quantum wells. <i>Applied Physics Letters</i> , 2000 , 76, 3040-3042	3-4	38
265	Origin of the significantly enhanced optical transitions in layered boron nitride. <i>Physical Review B</i> , 2012 , 86,	3-3	37
264	Hexagonal boron nitride and 6H-SiC heterostructures. <i>Applied Physics Letters</i> , 2013 , 102, 213505	3-4	37
263	High quality AlN for deep UV photodetectors. <i>Applied Physics Letters</i> , 2009 , 95, 054101	3-4	37
262	AlN avalanche photodetectors. <i>Applied Physics Letters</i> , 2007 , 91, 243503	3-4	37

261	Hybrid AlN/GaN deep ultraviolet Schottky barrier photodetectors. <i>Applied Physics Letters</i> , 2007 , 90, 263505	3.4	37
260	Excitation dynamics of the 1.54 μ m emission in Er doped GaN synthesized by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2007 , 90, 051110	3.4	37
259	Mechanism of enhanced luminescence in In _x Al _y Ga _{1-x-y} N quaternary epilayers. <i>Applied Physics Letters</i> , 2004 , 84, 1480-1482	3.4	37
258	The origins of near band-edge transitions in hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2016 , 108, 052106	3.4	37
257	Evolution of phase separation in In-rich InGaN alloys. <i>Applied Physics Letters</i> , 2010 , 96, 232105	3.4	36
256	Effects of plasma treatment on the Ohmic characteristics of Ti/Al/Ti/Au contacts to n-AlGaIn. <i>Applied Physics Letters</i> , 2006 , 89, 082109	3.4	36
255	Persistent photoconductivity in II-VI and III-V semiconductor alloys and a novel infrared detector. <i>Journal of Applied Physics</i> , 1991 , 69, 6701-6703	2.5	36
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253	Optical properties of strain-free AlN nanowires grown by molecular beam epitaxy on Si substrates. <i>Applied Physics Letters</i> , 2014 , 104, 223107	3.4	35
252	High mobility InN epilayers grown on AlN epilayer templates. <i>Applied Physics Letters</i> , 2008 , 92, 172101	3.4	35
251	Ultraviolet photoluminescence from ferromagnetic Fe-doped AlN nanorods. <i>Applied Physics Letters</i> , 2007 , 90, 193118	3.4	35
250	Cluster size and composition variations in yellow and red light-emitting InGaIn thin films upon thermal annealing. <i>Journal of Applied Physics</i> , 2004 , 95, 5388-5396	2.5	35
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244	Optical properties of GaN/AlGaIn multiple quantum well microdisks. <i>Applied Physics Letters</i> , 1997 , 71, 2898-2900	3.4	32

243	Effects of the wave function localization in AlInGaN quaternary alloys. <i>Applied Physics Letters</i> , 2007 , 91, 061125	3.4	32
242	Unintentionally doped n-type Al _{0.67} Ga _{0.33} N epilayers. <i>Applied Physics Letters</i> , 2005 , 86, 261902	3.4	32
241	Hexagonal boron nitride neutron detectors with high detection efficiencies. <i>Journal of Applied Physics</i> , 2018 , 123, 044501	2.5	31
240	Optical properties of the nitrogen vacancy in AlN epilayers. <i>Applied Physics Letters</i> , 2004 , 84, 1090-1092	3.4	31
239	Relaxation of stored charge carriers in a Zn _{0.3} Cd _{0.7} Se mixed crystal. <i>Physical Review B</i> , 1990 , 41, 5178-5187	3.7	31
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237	A Simplified Method of Making Flexible Blue LEDs on a Plastic Substrate. <i>IEEE Photonics Journal</i> , 2015 , 7, 1-7	1.8	30
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234	Growth and photoluminescence studies of Zn-doped AlN epilayers. <i>Applied Physics Letters</i> , 2006 , 89, 192111	3.4	30
233	Growth and photoluminescence studies of Al-rich Al _{1-x} Ga _x N quantum wells. <i>Applied Physics Letters</i> , 2006 , 89, 131922	3.4	30
232	Time-resolved photoluminescence studies of an ionized donor-bound exciton in GaN. <i>Applied Physics Letters</i> , 1999 , 74, 513-515	3.4	30
231	Large-Scale Growth of High-Quality Hexagonal Boron Nitride Crystals at Atmospheric Pressure from an FeCl ₃ Flux. <i>Crystal Growth and Design</i> , 2017 , 17, 4932-4935	3.5	29
230	Determination of energy-band offsets between GaN and AlN using excitonic luminescence transition in AlGa _x N alloys. <i>Journal of Applied Physics</i> , 2006 , 99, 013705	2.5	29
229	Temperature-dependent photoluminescence and electron field emission properties of AlN nanotip arrays. <i>Applied Physics Letters</i> , 2009 , 94, 173106	3.4	28
228	Photoluminescence properties of AlN homoepilayers with different orientations. <i>Applied Physics Letters</i> , 2008 , 93, 041905	3.4	28
227	AlGa _x N/GaN/AlN quantum-well field-effect transistors with highly resistive AlN epilayers. <i>Applied Physics Letters</i> , 2006 , 88, 073513	3.4	28
226	Effective mass of two-dimensional electron gas in an Al _{0.2} Ga _{0.8} N/GaN heterojunction. <i>Applied Physics Letters</i> , 2001 , 79, 66-68	3.4	28

225	Effects of persistent photoconductivity on the characteristic performance of an AlGa _N /Ga _N heterostructure ultraviolet detector. <i>Applied Physics Letters</i> , 1998 , 72, 2868-2870	3-4	28
224	Origin and roles of oxygen impurities in hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2018 , 112, 162103	3-4	27
223	Optical and magnetic behavior of erbium-doped Ga _N epilayers grown by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2007 , 91, 054106	3-4	27
222	III-nitride-based planar lightwave circuits for long wavelength optical communications. <i>IEEE Journal of Quantum Electronics</i> , 2005 , 41, 100-110	2	27
221	Effects of tensile, compressive, and zero strain on localized states in AlInGa _N /InGa _N quantum-well structures. <i>Applied Physics Letters</i> , 2002 , 80, 3099-3101	3-4	26
220	Strong-perturbation theory for impurities in semiconductors. <i>Physical Review B</i> , 1987 , 35, 9287-9290	3-3	26
219	Toward achieving flexible and high sensitivity hexagonal boron nitride neutron detectors. <i>Applied Physics Letters</i> , 2017 , 111, 033507	3-4	25
218	Growth and deep ultraviolet picosecond time-resolved photoluminescence studies of AlN/Ga _N multiple quantum wells. <i>Applied Physics Letters</i> , 2001 , 78, 3690-3692	3-4	25
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